

PUBLICATIONS

Peter W. Sutter

SUBMITTED OR IN PREPARATION

- [42] P. Sutter and P. Zahl, "Micron-Scale Atom-Resolved Scanning Tunneling Microscopy", Rev. Sci. Inst., in preparation.
- [41] P. Sutter, and P. Zahl, "Development of a Low-Temperature Multi-Terminal Scanning Tunneling Microscope", Rev. Sci. Inst., in preparation.
- [40] P. Sutter, "Growth of Semiconductor Heterostructures with Sharp Interfaces by Magnetron Sputter Epitaxy", J. Cryst. Growth, in preparation.

ACCEPTED FOR PUBLICATION

- [39] E. Sutter, P. Sutter, and J. E. Bernard, "Extended Shape Evolution of Low Mismatch $\text{Si}_{1-x}\text{Ge}_x$ Alloy Islands on Si(100)", Appl. Phys. Lett., accepted.
- [38] P. Sutter, E. Sutter, and T. Ohno, "High-Resolution Mapping of Nonuniform Carrier Transport at Contacts to Polycrystalline CdTe/CdS Solar Cells", Appl. Phys. Lett., accepted.

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- [37] P. Sutter, I. Schick, W. Ernst, and E. Sutter, "Initial Surface Roughening in Ge/Si(001) Heteroepitaxy Driven by Step-Vacancy Line Interaction", Phys. Rev. Lett. **91**, 176102 (2003).
- [36] P. Sutter, P. Zahl, and E. Sutter, "Continuous Formation and Faceting of SiGe Islands on Si(100)", Appl. Phys. Lett. **82**, 3454 (2003).
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